

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1962</b>	Ewing, R. I. 'Response of Silicon Surface Barrier Detectors to Hydrogen Ions of Energies 25 to 250 keV' <i>IEEE Trans. Nucl. Sci., NS-09, No. 3, 207-10 (1962)</i> <i>Comment : S. Rel. To H+. (70 keV/amu) H+2, H+3 -&gt; Si</i>	<b>1962-Ewin</b> 0513
<b>1963</b>	Primak, W. Dayal, Y. Edwards, E. 'Ion Bombardment of Silicon' <i>J. Appl. Phys., 34, 827-38 (1963)</i> <i>Comment : R. 100 keV H -&gt; Si</i>	<b>1963-Prim</b> 0570
<b>1964</b>	Dearnaley, G. 'The Channeling of Ions through Silicon Detectors' <i>IEEE Trans. Nucl. Sci., NS-11, 249-53 (1964)</i> <i>Comment : S, dS. 2 MeV H -&gt; Si (Cryst.)</i>	<b>1964-Dear</b> 0171
<b>1964</b>	Erginsoy, C. Wegner, H. E. Gibson, W. M. 'Anisotropic Energy Loss of Light Particles of MeV Energies in Thin Silicon Single Crystals' <i>Phys. Rev. Letters, 13, 530-34 (1964)</i> <i>Comment : S, dS. 2.8 MeV H -&gt; Si (Cryst.)</i>	<b>1964-Ergi</b> 0189
<b>1965</b>	Appleton, B. R. Erginsoy, C. Wegner, H. E. Gibson, W. M. 'Axial and Planar Effects in the Energy Loss of Protons in Silicon Single Crystals' <i>Phys. Letters, 19, 185-86 (1965)</i> <i>Comment : S, dS. 4.85 MeV H -&gt; Si (Cryst.)</i>	<b>1965-Appl</b> 0224
<b>1965</b>	Grew, G. W. 'Cyclotron Tests to Determine the Response of Solid-State Detectors to Protons of Energies 50 to 160 MeV for Use in a Proton Spectrometer' <i>IEEE Trans. Nucl. Sci., NS-12, 308-13 (1965)</i> <i>Comment : S,dS. 50-160 MeV H -&gt; Si</i>	<b>1965-Grew</b> 0515
<b>1965</b>	Wegner, H. E. Appleton, B. R. Erginsoy, C. Gibson, W. M. 'Axial and Planar Effects in the Energy Loss of Protons in Silicon Single Crystals' <i>Phys. Letters, 19, 187-89 (1965)</i> <i>Comment : S,dS. 4.85 MeV H -&gt; Si (Cryst.)</i>	<b>1965-Wegn</b> 0595
<b>1966</b>	Appleton, B. R. Altman, M. Feldman, L. C. Gibson, W. M. Erginsoy, C. 'Least Energy Loss and Its Dispersion for $\beta$ Channelled $\beta$ Protons in Silicon and Germanium Single Crystals' <i>Bull. Am. Phys. Soc., 11, 176 (1966)</i> <i>Comment : S, dS. 3-11 MeV H -&gt; Si, Ge (Both Cryst.)</i>	<b>1966-Appl</b> 0257

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1966</b>	Eisen, F. H. <b>'Channeling of 375 keV Protons through Silicon'</b> <i>Phys. Letters, 23, 401-02 (1966)</i> <i>Comment : S, dS. 375 keV H -&gt; Si (Cryst.)</i>	<b>1966-Eise</b> 0275
<b>1966</b>	Lander, R. L. Mehlhop, W. A. Lubatti, H. J. Schnurmacher, G. L. <b>'Solid-State Devices as Detectors of High-Energy Interactions'</b> <i>Nucl. Inst. Methods, 42, 261-68 (1966)</i> <i>Comment : dS. 760 MeV H -&gt; Si</i>	<b>1966-Land</b> 0423
<b>1966</b>	Maccabee, H. D. Raju, M. R. Tobias, C. A. <b>'Fluctuations of Energy Loss in Semiconductor Detectors'</b> <i>IEEE Trans. Nucl. Sci., NS-13, No. 6, 176-79 (1966)</i> <i>Comment : dS. 730 MeV H, 910 MeV He -&gt; Si</i>	<b>1966-Macc</b> 0730
<b>1967</b>	Marcinkowski, A. Rzewuski, H. Werner, Z. <b>'Range-Energy Relation for Low Energy Protons in Si and Ge'</b> <i>Nucl. Inst. Methods, 57, 338-40 (1967)</i> <i>Comment : R. 0.8 - 1.9 MeV H -&gt; Ge, Si.</i>	<b>1967-Marc</b> 0312
<b>1967</b>	Remillieux, J. Samuelli, J. J. Sarazin, A. <b>'Etude Des Effets Directionnels Dans La Transmission De Protons De 2 MeV a Travers Un Monocristal De Silicium'</b> <i>J. Physique, 28, 832-38 (1967)</i> <i>Comment : S, dS. 2 MeV H -&gt; Si (Cryst.)</i>	<b>1967-Remi</b> 0602
<b>1968</b>	Kolats, J. J. Amos, T. M. Bichsel, H. <b>'Energy-Loss Straggling of Protons in Silicon'</b> <i>Phys. Rev., 176, 484-89 (1968)</i> <i>Comment : dS. 5-42 MeV H -&gt; Si</i>	<b>1968-Kola</b> 0372
<b>1968</b>	Maccabee, H. D. Raju, M. R. Tobias, C. H. <b>'Fluctuations of Energy Loss by Heavy Charged Particles in Thin Absorbers'</b> <i>Phys. Rev., 165, 469-74 (1968)</i> <i>Comment : dS. 45, 730 MeV H, 910 MeV He, 370 MeV Pi- -&gt; Si</i>	<b>1968-Macc</b> 0314
<b>1968</b>	Mannami, M. Fujimoto, F. Ozawa, K. <b>'Anomalous Energy Losses of 1.5 MeV Protons Channeled in Silicon Single Crystals.'</b> <i>Phys. Letters A, 26, 201-02 (1968)</i> <i>Comment : S, dS. 1.5 MeV H -&gt; Si (Cryst.)</i>	<b>1968-Mann</b> 0320
<b>1968</b>	Sattler, A. R. Dearnaley, G. <b>'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si'</b> <i>Phys. Rev., 161, 244-52 (1967)(Erratum, Phys. Rev., 165, 750 (1968))</i> <i>Comment : S. 4-7.6 MeV H, D -&gt; Ge, GaAs, Si (All Cryst.)</i>	<b>1968-Satt</b> 0308

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb		
<b>1968</b>	Shipatov, E. T. Kononov, B. A. <b>'Investigation of the Channeling of Protons in Single Crystals of Ionic Compounds and Semiconductors'</b> <i>Izv. Vuz. Fiz. No. 9, 52-56 (1968). [Engl. Trans. Soviet Phys. J. No. 9, 46-49, (1968)]</i> <i>Comment : S,dS. H (4.7-6.7 MeV) -&gt; NaCl, KCl, KBr, Si, Ge (crystals)</i>	<table border="1"> <tr><td style="text-align: center;"><b>1968-Ship2</b></td></tr> <tr><td style="text-align: center;">0599</td></tr> </table>	<b>1968-Ship2</b>	0599
<b>1968-Ship2</b>				
0599				
<b>1968</b>	Shipatov, E. T. Kononov, B. A. <b>'Energy Distribution of 6.72 MeV Protons Passing through Monocrystals.'</b> <i>Atomnaya Energiya (USSR), 25, 439-40 (1968) [Engl. Trans. Sov. Atom. Energy, 25, 1254-55 (1968).</i> <i>Comment : S, dS. 6.72 MeV H -&gt; NaCl, KCl, KBr, Si, Ge (All Cryst.)</i>	<table border="1"> <tr><td style="text-align: center;"><b>1968-Ship3</b></td></tr> <tr><td style="text-align: center;">0653</td></tr> </table>	<b>1968-Ship3</b>	0653
<b>1968-Ship3</b>				
0653				
<b>1968</b>	Tschalar, C. Bichsel, H. <b>'Mean Excitation Potential of Light Compounds'</b> <i>Phys. Rev., 175, 476-8 (1968)</i> <i>Comment : R. 3-30 MeV H -&gt; Si, Al, SiO2, Al2O3, C3H5O2</i>	<table border="1"> <tr><td style="text-align: center;"><b>1968-Tsch3</b></td></tr> <tr><td style="text-align: center;">0904</td></tr> </table>	<b>1968-Tsch3</b>	0904
<b>1968-Tsch3</b>				
0904				
<b>1969</b>	Aitken, D. W. Lakin, W. L. Zulliger, H. R. <b>'Energy Loss and Stragglng in Silicon by High-Energy Electrons, Positive Pions, and Protons'</b> <i>Phys. Rev., 179, 393-98 (1969)</i> <i>Comment : S, dS. 29-300 MeV H, 50-200 MeV Pi+ -&gt; Si</i>	<table border="1"> <tr><td style="text-align: center;"><b>1969-Aitk</b></td></tr> <tr><td style="text-align: center;">0385</td></tr> </table>	<b>1969-Aitk</b>	0385
<b>1969-Aitk</b>				
0385				
<b>1969</b>	Arkhipov, E. P. Gott, Yu. V. <b>'Slowing Down of 0.5 - 30 keV Protons in Some Materials.'</b> <i>Zh. Eksp. Teor. Fiz., 56, 1146-51 (1969). [Engl. Trans. Sov. Phys. JETP, 29, 615-18 (1969)</i> <i>Comment : S. 0.5-30 keV H -&gt; C, Ti, Al, Cu, Ni, Fe, Ge, Si, Sb, Bi</i>	<table border="1"> <tr><td style="text-align: center;"><b>1969-ArkH</b></td></tr> <tr><td style="text-align: center;">0410</td></tr> </table>	<b>1969-ArkH</b>	0410
<b>1969-ArkH</b>				
0410				
<b>1969</b>	Clark, G. J. Dearnaley, G. Morgan, D. V. Poate, J. M. <b>'The Stopping Power of Protons Channelled through Csi Crystals'</b> <i>Phys. Letters A, 30, 11-12 (1969)</i> <i>Comment : S. 4 MeV H -&gt; Si (Cryst.)</i>	<table border="1"> <tr><td style="text-align: center;"><b>1969-Clar</b></td></tr> <tr><td style="text-align: center;">0127</td></tr> </table>	<b>1969-Clar</b>	0127
<b>1969-Clar</b>				
0127				
<b>1969</b>	Shipatov, E. T. <b>'Energy and Angular Distributions of Protons Transmitted by Germanium and Silicon Single Crystals Along (110) and (100) Channels in the Crystal Lattice'</b> <i>Fiz. Tekh. Poluprovodnikov, 2, 1690-91 (1968). [Engl. Trans. Sov. Phys. Semicond., 2, 1408-09 (1969)</i> <i>Comment : S, dS. 6.72 MeV H -&gt; Si, Ge (Both Cryst.)</i>	<table border="1"> <tr><td style="text-align: center;"><b>1969-Ship2</b></td></tr> <tr><td style="text-align: center;">0654</td></tr> </table>	<b>1969-Ship2</b>	0654
<b>1969-Ship2</b>				
0654				
<b>1970</b>	Kononov, B. A. Struts, V. K. <b>'Channeling of Protons in Silicon at Different Temperatures'</b> <i>Izv. Vuz. Fiz. No. 6, 60-63 (1970). [Engl. Trans. Sov. Phys. J., 13, 738-61 (1970)]</i> <i>Comment : S, dS. 6.72 MeV H -&gt; Si (Cryst.)</i>	<table border="1"> <tr><td style="text-align: center;"><b>1970-Kono</b></td></tr> <tr><td style="text-align: center;">0646</td></tr> </table>	<b>1970-Kono</b>	0646
<b>1970-Kono</b>				
0646				

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1971</b>	Chemin, J. F. Roturier, J. Petit, G. Y. <b>'Mesure par Reactions Nucleaires Resonnantes du Relentissement et de la Dispersion en Energie de Protons'</b> <i>J. Phys. (Paris), 32, 220 (1971)</i> <i>Comment : S,dS. H (1-4 MeV) -&gt; Si.</i>	<b>1971-Chem</b> 1634
<b>1971</b>	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. <b>'Energy Loss of H, D, and 4He Ions Channeled through Thin Single Crystals of Silicon'</b> <i>Phys. Rev. Letters, 27, 1194-96 (1971)</i> <i>Comment : S. 0.9-5.0 MeV H, D, He -&gt; Si Cryst. And Amorph.</i>	<b>1971-Dell</b> 0132
<b>1971</b>	Moline, R. A. <b>'Ion-Implanted Phosphorous in Silicon: Profiles using C-V Analysis'</b> <i>J. Appl. Phys., 42, 3553-58 (1971)</i> <i>Comment : R. 200, 300, 600 keV H -&gt; Si</i>	<b>1971-Moli</b> 0952
<b>1972</b>	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. <b>'Indirect Determination of the Energy Loss of Protons Channeled in Silicon Crystals'</b> <i>Rendiconti Della Academia Nazionale Dei Lincei. Classe Di Scienze Fisiche Matematiche E Naturali. Ser. 8,, , 52, No. 5, P. 727-33 (1972)</i> <i>Comment : S. 1600 keV H -&gt; Si (Cryst.)</i>	<b>1972-Dell</b> 0463
<b>1972</b>	Foster, C. Kool, W. H. VanDerWeg, W. F. Roosendaal, E. <b>'Random Stopping Power for Protons in Silicon'</b> <i>Rad. Effects, 16, 139-40 (1972)</i> <i>Comment : S. 120 keV H -&gt; Si</i>	<b>1972-Fost</b> 0466
<b>1972</b>	Minear, R. L. Nelson, D. G. Gibbons, J. F. <b>'Enhanced Diffusion in Si and Ge by Light Ion Implantation'</b> <i>J. Appl. Phys., 43, 3468-3480 (1972)</i> <i>Comment : R, dR. 70-150 keV H, D, H2 -&gt; Si, Ge</i>	<b>1972-Mine</b> 0999
<b>1972</b>	Sone, K. Fukusawa, F. <b>'Transmission of Fast Protons through Si Single Crystals'</b> <i>Mem Fac. Eng. Kyoto Univ., 34, 325-32 (1972)</i> <i>Comment : S, dS. 3 MeV H -&gt; Si (Cryst.)</i>	<b>1972-Sone</b> 0693
<b>1973</b>	Bottiger, J. Eisen, F. H. <b>'On Conversion from an Energy Scale to a Depth Scale in Channeling Experiments'</b> <i>Thin Solid Films, 19, 239-246 (1973)</i> <i>Comment : S. 0.2-0.4 MeV H -&gt; Si (Cryst.)</i>	<b>1973-Bott</b> 0507
<b>1973</b>	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. <b>'Axial- to Planar-Channeling Transition'</b> <i>Phys. Rev. B, 7, 4029-4041 (1973)</i> <i>Comment : R. 1-2.8 MeV H -&gt; Si</i>	<b>1973-Dell</b> 0961

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb		
<b>1974</b>	<p>Bulgakov, Yu. V. Nikolaev, V. S. Shulga, V. I.  <b>'The Experimental Determination of the Impact Parameter Dependence of Inelastic Energy Loss of Channeled Ions'</b>  <i>Phys. Letters A, 46, 477-78 (1974)</i></p> <p><i>Comment : S, dS. 1.15, 1.75 MeV H, 5.7 MeV N -&gt; Si (Cryst.)</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1974-Bulg</b></td> </tr> <tr> <td style="text-align: center;">0668</td> </tr> </table>	<b>1974-Bulg</b>	0668
<b>1974-Bulg</b>				
0668				
<b>1974</b>	<p>Castaing, C. Baruch, P. Picard, C.  <b>'Mesures Experimentales De La Penetration Des Protons Dans Le Silicum'</b>  <i>Le Vide, 171 Suppl, 61 (1974)</i></p> <p><i>Comment : R. 200-600 keV H -&gt; Si. Ranges From Pit-Depth After Blistering Of Silicon.</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1974-Cast</b></td> </tr> <tr> <td style="text-align: center;">0949</td> </tr> </table>	<b>1974-Cast</b>	0949
<b>1974-Cast</b>				
0949				
<b>1974</b>	<p>Guivarc'H, E. Ligeon A.  <b>'A New Utilization of 11B Ion Beams: Hydrogen Analysis by 1H(11B,alpha)alpha,alpha Nuclear Reaction'</b>  <i>Rad. Effects, 22, 101-105 (1974)</i></p> <p><i>Comment : R, dR. 10 keV H -&gt; Si</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1974-Guiv</b></td> </tr> <tr> <td style="text-align: center;">0801</td> </tr> </table>	<b>1974-Guiv</b>	0801
<b>1974-Guiv</b>				
0801				
<b>1975</b>	<p>DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G.  <b>'Transmission Energy Loss of Protons Channeled in Thin Silicon Single Crystals of Medium Energy'</b>  <i>Datz, B. R. Appleton, C. D. Moak (Ed.): Atomic Collisions in Solids. Plenum N. Y., 75-76 (1975)</i></p> <p><i>Comment : S. 50-300 keV H -&gt; Si (Cryst.) Chann. To Random Ratio</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1975-Dell</b></td> </tr> <tr> <td style="text-align: center;">0574</td> </tr> </table>	<b>1975-Dell</b>	0574
<b>1975-Dell</b>				
0574				
<b>1975</b>	<p>Eisen, F. H. Bottiger, J.  <b>'Transmission Energy Spectra of Channeled Protons Scattered in Thin Silicon Films'</b>  <i>Atomic Collisions in Solids, Plenum Press, 919-27 (1975)</i></p> <p><i>Comment : S,dS. 200, 400 keV H -&gt; Si (Cryst.)</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1975-Eise</b></td> </tr> <tr> <td style="text-align: center;">0579</td> </tr> </table>	<b>1975-Eise</b>	0579
<b>1975-Eise</b>				
0579				
<b>1975</b>	<p>Gotz, V. G. Klinge, K. D. Schwabe, F.  <b>'Measurement of the Energy Loss in Thin Silicon Single Crystals'</b>  <i>Exp. Tech. Phys., 23, 167-169 (1975)</i></p> <p><i>Comment : S. 0.7-1.6 MeV H -&gt; Si</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1975-Gotz</b></td> </tr> <tr> <td style="text-align: center;">1017</td> </tr> </table>	<b>1975-Gotz</b>	1017
<b>1975-Gotz</b>				
1017				
<b>1975</b>	<p>Gotz, G. Klinge, K. D. Finger, U.  <b>'A Combination of Dechanneling and Energy Measurements of Protons in Thin Silicon Single Crystals.'</b>  <i>Atomic Collisions in Solids, Plenum Press, 693-716 (1975)</i></p> <p><i>Comment : S. 0.7-1.8 MeV H -&gt; Si (Cryst.) Chann. To Random Ratio.</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1975-Gotz2</b></td> </tr> <tr> <td style="text-align: center;">0577</td> </tr> </table>	<b>1975-Gotz2</b>	0577
<b>1975-Gotz2</b>				
0577				
<b>1975</b>	<p>Melvin, J. D.  <b>'Energy Loss of Light Ions Channeling in Silicon'</b>  <i>Ph.D., Cal. Inst. Tech., Unpublished (1975)</i></p> <p><i>Comment : S, dS. 0.5-1.6 MeV H -&gt; Si (110), (111), (211)</i></p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center;"><b>1975-Melv</b></td> </tr> <tr> <td style="text-align: center;">1271</td> </tr> </table>	<b>1975-Melv</b>	1271
<b>1975-Melv</b>				
1271				

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1975</b>	Melvin, J. D. Tombrello, T. A. <b>'Energy Loss of Low Energy Protons Channeling in Silicon Crystals'</b> <i>Rad. Effects, 26, 113-26 (1975)</i> <i>Comment : S. 0.5-1.6 MeV H -&gt; Si (Cryst.)</i>	<b>1975-Melv2</b> 0757
<b>1976</b>	Grahmann, G. Kalbitzer, S. <b>'Nuclear and Electronic Stopping Powers of Low Energy Ions with Z &lt;= 10 in Silicon'</b> <i>Nucl. Inst. Methods, 132, 119-23 (1976)</i> <i>Comment : S. 2-60 keV H, He, B, C, N, Ne -&gt; Si</i>	<b>1976-Grah</b> 0871
<b>1976</b>	Hasegawa, S. Ishiwara, H. Furukawa, S. Shimizu, T. <b>'The Lattice Location of Phosphorus Atoms Implanted into Silicon'</b> <i>Jap. J. Appl. Phys., 15, 391-92 (1976)</i> <i>Comment : R. 100 keV P -&gt; Si</i>	<b>1976-Hase</b> 0858
<b>1976</b>	Lanford, W. A. Trautvetter, H. P. Ziegler, J. F. Keller, J. <b>'A New Precision Technique for Measuring the Concentration Versus Depth of Hydrogen in Solids'</b> <i>Appl. Phys. Letters, 28, 566-68 (1976)</i> <i>Comment : R, dR. 7.5 keV H -&gt; Si (Cryst.)</i>	<b>1976-Lanf</b> 0824
<b>1976</b>	Ligeon, E. Guivarc'H, A. <b>'Hydrogen Implantation in Silicon Between 1.5 - 60 keV.'</b> <i>Rad. Effects, 27, 129-37 (1976)</i> <i>Comment : S,R,dR. 1.5-60 keV H -&gt; Si. S. 1.5-60 keV H, 2.0 MeV 11B -&gt; Si</i>	<b>1976-Lige</b> 0817
<b>1976</b>	Mende, G. Kuster, G. <b>'Die Abtragung Dunner Schichten von P- und B-Implantierten Silizium Mit Hilfe der Anodischen Oxydation'</b> <i>Thin Solid Films, 35, 215-220 (1976)</i> <i>Comment : R, dR. 30 keV H -&gt; Si</i>	<b>1976-Mend</b> 0875
<b>1976</b>	Wilken, B. Fritz, T. A. <b>'Energy Distribution Functions of Low Energy Ions in Silicon Absorbers Measured for Large Relative Energy Losses'</b> <i>Nucl. Inst. Methods, 138, 331-343 (1976)</i> <i>Comment : dS. 300 keV-1.5 MeV H, 3He -&gt; Si</i>	<b>1976-Wilk</b> 1051
<b>1977</b>	Cembali, F. Zignani, F. <b>'Determination of Random and Aligned Stopping Powers for 80-300 keV Protons in Silicon by Backscattering Measurements'</b> <i>Rad. Effects, 31, 169-173 (1977)</i> <i>Comment : S. 80-300 keV H -&gt; Si Single Crystal ([110], [100], [111], and Random)</i>	<b>1977-Cemb</b> 1033
<b>1977</b>	Chu, W. K. Kastl, R. H. Lever, R. F. Mader, S. Masters, B. J. <b>'Distribution of Irradiation Damage in Silicon Bombarded with Hydrogen'</b> <i>Phys. Rev. B, 16, 3851-3859 (1977)</i> <i>Comment : R. 50-250 keV H -&gt; Si [001]. Ranges From Profiling Of Lattice Damage.</i>	<b>1977-Chu</b> 1037

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1977</b>	Grigor'eva, G. M. Kolodin, L. G. kreinin, L. B. Mukashev, B. N. Nusupov, K. Kh. <b>'Radiation Defects in p-type Silicon Irradiated with 30 MeV Protons'</b> <i>Sov. Phys. Semicond., 11 (11), 1278-1280 (1977)</i> <i>Comment : R,dR. H (30 MeV) -&gt; Si</i>	<b>1977-Grig</b>  2127
<b>1977</b>	Thompson, D. A. Robinson, J. E. Walker, R. S. <b>'Inelastic Stopping of Medium Energy Light Ions in Silicon'</b> <i>Rad. Effects, 32, 169-175 (1977)</i> <i>Comment : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -&gt; Si</i>	<b>1977-Thom</b>  1076
<b>1978</b>	Carnera, A. Della Mea, G. Drigo, A. V. Lo Russo, S. Mazzoldi, P. <b>'Channeled and Random Proton Stopping Power in Si in the 300-1000 keV Energy Range'</b> <i>Phys. Rev. B, 17, 3492 (1978)</i> <i>Comment : S. H (40-900 keV) -&gt; Si. Channeled and Random stopping powers.</i>	<b>1978-Carn</b>  1631
<b>1978</b>	Cembali, F. Dori, L. Galloni, R. Servidori, M. Zignani, F. <b>'Radiation Damage in Silicon Produced by Phosphorus Implantation: Random and Aligned Implants'</b> <i>Rad. Effects, 36, 111-117 (1978)</i> <i>Comment : R. 200 keV P -&gt; Si</i>	<b>1978-Cemb</b>  1109
<b>1978</b>	Chu, W. K. Kastl, R. H. Lever, R. F. Mader, S. Masters, B. J. <b>'Damage Profiling for Hydrogen Implanted in Silicon'</b> <i>Phys. Rev. B, (1978)</i> <i>Comment : R, dR. 50 - 250 keV H -&gt; Si. (Damage Dist. Of H Implantation)</i>	<b>1978-Chu 2</b>  0932
<b>1978</b>	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. <b>'Channeling of Fast Protons, Deuterons and Alpha Particles'</b> <i>Preprint (1978)</i> <i>Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -&gt; Si</i>	<b>1978-Jarv</b>  1148
<b>1978</b>	Langley, R. A. Brice, D. K. <b>'Energy Straggling of Protons in Be, C, Al, Si'</b> <i>Phys. Rev. B, 18, 4673 (1978)</i> <i>Comment : dS. (.5-2.5 MeV) H -&gt; Be, C, Al, Si</i>	<b>1978-Lang3</b>  1149
<b>1978</b>	Mittenbacher, J. Gartner, K. <b>'Proton Ranges in Silicon and in Si-SiO<sub>2</sub> Double Layers'</b> <i>Intl. Conf. Ion Beam Modification of Materials, Budapest -c (1978)</i> <i>Comment : R. 40-700 keV H -&gt; Si, SiO<sub>2</sub></i>	<b>1978-Mitt</b>  1175
<b>1978</b>	Nashiyama, I. <b>'Depth Profile Analysis of Proton Damage by Channeling'</b> <i>Phys. Rev. B, 17, 104-110 (1978)</i> <i>Comment : R. 0.8-1.2 MeV H<sub>3</sub> -&gt; Si. Ranges Of Lattice Damage.</i>	<b>1978-Nash</b>  1105

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1978</b>	Ziegler, J. F. Wu, C. P. Williams, P. White, C. W. Terreault, B. <b>'Profiling Hydrogen in Materials using Ion Beams'</b> <i>Nucl. Inst. Methods, 149, 19-39 (1978)</i> <i>Comment : R. 40 keV H, 31 keV D -&gt; Si. Multiple-Technique. A Definitive Effort.</i>	<b>1978-Zieg</b> 0960
<b>1979</b>	Doyle, B. L. Peercy, P. S. <b>'Technique for Profiling 1H with 2.5 MeV van de Graaff Accelerators.'</b> <i>Appl. Phys. Letters, 34, 811-813 (1979)</i> <i>Comment : R. 1-3 MeV H -&gt; Si3N4, Si</i>	<b>1979-Doyl</b> 1135
<b>1979</b>	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. <b>'Channeling of Fast Protons, Deuterons, and Alpha Particles'</b> <i>Phys. Rev. B, 19, 5559-5577 (1979)</i> <i>Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -&gt; Si</i>	<b>1979-Jarv</b> 1199
<b>1979</b>	Magee, C. W. <b>'Depth Profiling of N-Type Dopants in Si and GaAs using Cs+ Bombardment Negative Secondary Ion Mass Spectrometry in Ultrahigh Vacuum'</b> <i>J. Electrochem. Soc., 126, 660-663 (1979)</i> <i>Comment : R, dR. 15 keV H, 80 keV P, 200 keV As -&gt; Si; 200 keV Si, 250 keV S -&gt; GaAs</i>	<b>1979-Mage</b> 1223
<b>1979</b>	Stein, H. J. Peercy, P. S. <b>'Controlled Hydrogenation of Amorphous Silicon at Low Temperatures'</b> <i>Appl. Phys. Letters, 34, 604-606 (1979)</i> <i>Comment : R, dR. 20 keV H -&gt; Si</i>	<b>1979-Stei</b> 1140
<b>1980</b>	Demond, F. J. Kalbitzer, S. Mannsperger, H. Muller, G. <b>'Range Parameters of Protons in Silicon Implanted at Energies from 0.5 to 300 keV.'</b> <i>Nucl. Inst. Methods, 168, 69-74 (1980)</i> <i>Comment : R, dR. .5-300 keV H -&gt; Si</i>	<b>1980-Demo</b> 1309
<b>1980</b>	Izmailov, Sh. Z. Sirotinin, E. I. Tulinov, A. F. <b>'Energy Loss of Protons in Si, Ge, and Mo'</b> <i>Nucl. Inst. Methods, 168, 81-84 (1980)</i> <i>Comment : S, dS. .1-1 MeV H -&gt; Si, Ge, Mo</i>	<b>1980-Izma</b> 1342
<b>1980</b>	Josquin, W. J. M. J. <b>'The Oxidation Characteristics of Nitrogen-Implanted Silicon'</b> <i>Rad. Effects, 47, 221-224, (1980)</i> <i>Comment : R, dR. 250-800 keV H, H2, He, B, P -&gt; Si</i>	<b>1980-Josq</b> 1331
<b>1980</b>	MaGee, C. W. Cohen, S. A. Voss, D. E. Brice, D. K. <b>'Depth Distributions of Low Energy Deuterium Implanted into Silicon as Determined by SIMS'</b> <i>Nucl. Inst. Methods, 168, 383-387 (1980)</i> <i>Comment : R, dR. D (0.1-5 keV) -&gt; Si</i>	<b>1980-MaGe</b> 1529



# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1980</b>	Percy, P. S. Stein, H. J. Ginley, D. S. <b>'Effect of Disorder on the Hydrogen Content in Si'</b> <i>Appl. Phys. Letters, 36, 678-680 (1980)</i> Comment : R, dR. 150-300 keV H -> Si	<b>1980-Peer</b> 1335
<b>1980</b>	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. <b>'Charge-Exchange Effects in Energy-Loss Straggling'</b> <i>Nucl. Inst. Methods, 170, 221-225 (1980)</i> Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al	<b>1980-Sofi</b> 1378
<b>1981</b>	Kuhrt, E. Lenkeit, K. Taubner, F. <b>'Measurements of the Stopping Power of 40-300 keV Protons in Silicon'</b> <i>Phys. Stat. Sol. A, 66, 131 (1981)</i> Comment : S. H (40-300 keV) -> Si	<b>1981-Kuhr</b> 1694
<b>1981</b>	Pearce, J. D. Hart, R. R. <b>'Stopping Power Measurements in the 20-150 keV Region using Thick Target Backscattering: H and He on C, Si and Au'</b> <i>J. Appl. Phys., 52, 5056 (1981)</i> Comment : S. H, He (20-150 keV) -> C, Si, Au	<b>1981-Pear</b> 1736
<b>1981</b>	Santry, D. C. Werner, R. D. <b>'Stopping Powers of C, Al, Si, Ti, Ni, Ag and Au for Deuterons'</b> <i>Nucl. Inst. Methods, 188, 211 (1981)</i> Comment : S. D (0.2-2.0 MeV) -> C, Al, Si, Ti, Ni, Ag, Au	<b>1981-Sant</b> 1756
<b>1983</b>	Hancock, S. James, F. Movchet, J. Rancoita, P. G. Van Rossum, L. <b>'Energy Loss and Energy Straggling of Protons and Pions in the Momentum Range 0.7-115 GeV/c'</b> <i>Phys. Rev. A, 28, 615</i> Comment : S,dS. H, pions (0.7-115 GeV/c) -> Si	<b>1983-Hanc</b> 1659
<b>1983</b>	Mannsperger, H. Kalbitzer, S. Demond, F. J. Damjantschitsch, H. <b>'Projection Factors of Low Energy Ion Ranges'</b> <i>Nucl. Inst. Methods, 209/210, 49-55 (1983)</i> Comment : R. H, C, Na, Al, Si, Ar, Cr (.04<epsilon<1) -> Si, Ge	<b>1983-Mann</b> 2199
<b>1984</b>	Heidemann, K. F. Gruner, M. Kaat, E. <b>'Optical Characterization of Damage and Concentration Profiles in H Ion Implanted Amorphous Silicon'</b> <i>Rad. Effects, 82, 103-131 (1984)</i> Comment : R, dR. H (190 keV) -> Si (Optical Characterization)	<b>1984-Heid</b> 1519
<b>1984</b>	Sirotnin, E. I. Tulinov, A. F. Khodyrev, V. A. Mizgulin, V. N. <b>'Proton Energy Loss in Solids'</b> <i>Nucl. Inst. Methods, B4, 337 (1984) -1</i> Comment : S. H (0.1-6.0 MeV) -> Al, Si, Sc, V, Cu, Zn, Ga, Ge, Y, Zr, Nb, Mo, Ag, Cd, In, Sn, La, Sm, Gd, Yb, Hf, Ta, W, Pt, Au, Pb	<b>1984-Siro</b> 1770

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1985</b>	Gehrmann, P. Lenkeit, K. Stolle, R. 'Measurement of Proton Channeling Energy Losses in Silicon in the Intermedicate Energy Region' <i>Phys. Stat. Sol. B, 131, 519 (1985)</i> <i>Comment : S. H (40-350 keV) -&gt; Si. Channeled stopping powers.</i>	<b>1985-Gehr</b> 1963
<b>1985</b>	Hautala, M. Keinonen, J. Whitlow, H. J. Tikkanen, P. Uhrmacher, M. 'Range Profiles of 25-250 keV Hydrogen in Silicon' <i>Phys. Letters, 109A, 344-346 (1985)</i> <i>Comment : R, dR. H (25-250 keV) -&gt; Si</i>	<b>1985-Haut</b> 1534
<b>1987</b>	Weiser, M. Behar, M. Kalbitzer, S. Oberschachtsiek, P. Fink, D. 'A Four-Moments Analysis of H Range Profiles in Silicon' <i>Nucl. Inst. Methods, B29, 587-590 (1987)</i> <i>Comment : R. H (25-300 keV) -&gt; Si</i>	<b>1987-Weis</b> 2197
<b>1988</b>	Mertens, P. Bauer, P. 'Reference Stopping Cross Sections for 30-600 keV Protons in Silicon' <i>Nucl. Inst. Methods, B33, 133 (1988)</i> <i>Comment : S. H (30-600 keV) -&gt; Si</i>	<b>1988-Mert</b> 1720
<b>1989</b>	Weiser, M. Oberschachtsiek, P. Gunzler, R. Schule, V. Kalbitzer, S. 'Experimental and Calculated Range Moments of Deep Implants' <i>Mater. Sci. Eng., B2, 55-61 (1989)</i> <i>Comment : R. H, N, I, Au (.2-5 MeV) -&gt; Si Range distributions/moments.</i>	<b>1989-Weis</b> 2196
<b>1990</b>	Bauer, P. 'Stopping Power of Light Ions near the Maximum' <i>Nucl. Inst. Methods, B45, 673 (1990)</i> <i>Comment : dS. H, H- (30-700 keV) -&gt; C, Al, Si, Ni, Cu, Ag, Au, SiO2, HC2, Al2O3</i>	<b>1990-Baue</b> 1608
<b>1991</b>	Medenwaldt, R. Moller, S. P. Uggerhoj, E. Worn, T. Hvelplund, P. 'Measurement of the Stopping Power of Silicon for Antiprotons between 0.2 - 3 MeV' <i>Nucl. Inst. Methods, B58, 1-5 (1991)</i> <i>Comment : S. H-( 0.2-3 MeV) -&gt; Si Anti-proton stopping powers.</i>	<b>1991-Mede</b> 1716
<b>1992</b>	Bichsel, H. Hiraoka, T. 'Energy Loss of 70 MeV Protons in Elements' <i>Nucl. Inst. Methods, B66, 345-351 (1992)</i> <i>Comment : S. H (70 MeV) -&gt; C, H2O, SiO2, Al, Si, Ti, Cr, Fe, Co, Ni, Cu, Zn, Zr, Nb, Mo, Ag, Cd, In, Sn, Ta, W, Pb</i>	<b>1992-Bich2</b> 1624
<b>1992</b>	Santry, D. C. Werner, R. D. 'Measured Stopping Powers of O-16 and F-19 Ions in Thin Elemental Films' <i>Nucl. Inst. Methods, B69, 167-173 (1992)</i> <i>Comment : S. O, F (200-2000 keV) -&gt; Be, C, Al, Si, Ni, Ti, Ag, Au</i>	<b>1992-Sant</b> 1887

# Citations for Ion = **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1993</b>	Narumi, K. Fujii, Y. Kishine, K. Fujiwara, S. Kimura, K. <b>'Energy Losses of 12-32 keV H, He and N Ions at Glancing Angle Scattering from Clean Surfaces of Silicon Crystals'</b> <i>J. Phys. Soc. Jap., 62, 1603-1611 (1993)</i> <i>Comment : S. H, He, N (12-32 keV) -&gt; Si Surface scattering effects</i>	<b>1993-Naru</b> 2054
<b>1994</b>	Avdeichikov, V. V. Bergholt, L. Guttormsen, M. Taylor, J. E. Westerberg, L. <b>'Light Output and Energy Resolution of CsI, YAG, GSO, BGO, LSO Scintillators for Light Ions'</b> <i>Nucl. Inst. Methods, A349, 216-224 (1994)</i> <i>Comment : S. H, D, He (3-20 MeV/amu)-&gt; CsI, YAG, GSO, BGO, LSO Scintillators</i>	<b>1994-Avde</b> 2074
<b>1995</b>	Shevchenko, V. A. <b>'Stopping Power Measurements of Low Energy Protons using Backscattering on the Target'</b> <i>Metall-Novei.-Tekh., 17, 27-29 (1995) Translated in "Physics of Metals"</i> <i>Comment : S. H (80-240 keV) -&gt; Si, Cd, Fe, Au, YBaCuO</i>	<b>1995-Shev</b> 2378
<b>1996</b>	Ikeda, A. Sumitomo, K. Nishioka, T. Kido, Y. <b>'Stopping Powers and Energy Straggling for 50-300 keV H in Amorphous Si and Ge Films'</b> <i>Nucl. Inst. Methods, B115, 34-38 (1996)</i> <i>Comment : S, dS. H (50-300 keV) -&gt; Si, Ge</i>	<b>1996-Iked</b> 2029
<b>1996</b>	Misdaq, M. A. Ellassali, R. <b>'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods'</b> <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> <i>Comment : S. Light ions -&gt; Si, GaAs (channeled)</i>	<b>1996-Misd</b> 0964
<b>1996</b>	Niemann, D. Kinac, G. Kalbitzer, S. <b>'Stopping Power of H, He and N in Si in the Energy Range of 0.02-1.0 MeV/amu'</b> <i>Nucl. Inst. Methods, 118, 11-18 (1996)</i> <i>Comment : S. H, He, N (.02-1.0 MeV/amu) -&gt; Si</i>	<b>1996-Niem</b> 1101
<b>1997</b>	Dos Santos, J. H. R. Behar, M. Grande, P. L. Boudinov, H. Kalbitzer, S. <b>'Electronic Stopping Power of B in Si in Random and &lt;100&gt; Channeling Directions'</b> <i>Phys. Rev., B55, 13651-13657 (1997)</i> <i>Comment : S. B (500 - 9000 keV) -&gt; Si Random and Channeled</i>	<b>1997-Dos</b> 0921
<b>1997</b>	Moller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. <b>'Direct Measurements of the Stopping Power for Antiprotons of Light and Heavy Targets'</b> <i>Phys. Rev. A, 56, 2930-2939 (1997)</i> <i>Comment : S. H- (50 - 700 keV) -&gt; Al, Si, Ti, Cu, Ag, Ta, Pt, Au</i>	<b>1997-Moll</b> 2364

*Citations for Ion = **H** , Target = **Si***

<i>Pub. Year</i>	<i>Authors, Title, Journal Citation and Comments</i>	<i>Citation Numb</i>
<b>1997</b>	Muller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. <b>'Measurement of the Barkas Effect Around the Stopping Power Maximum for Light and Heavy Targets'</b> <i>Nucl. Inst. Methods, B122, 162-166 (1997)</i> <i>Comment : S. H- (50-700 keV) -&gt; Si, Au</i>	<b>1997-Mull</b> 2026